IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

John F. Conley, Jr., Yoshi Ono, and

Wei Gao

Serial No: Not Yet Assigned

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Inventors:

Herewith

Title:

REACTIVE GATE ELECTRODE

CONDUCTIVE BARRIER

PATENT APPLICATION

Attorney Docket No. SLA0674

Hon. Commissioner for Patents Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by the Examiner and made of record in the above-identified application.

February 23, 2004

(Date)

Respectfully submitted

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FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER SLA674 APPLICATION NUMBER APPLICANT Conley et al.			
				FILING DATE:	GROUP ART UNIT		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE		NAME	CLASS	SUB CLASS	FIL. DATE IF APPROP.
		FOREIGN	L DATENI	T DOCUMENTS			
FOREIGN PATE DOCUMENT DATE NUMBER			PATEN	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO
OTHER DOCUMENTS							
V. Misra, G.P. Heuss, H. Zhong, "Use of metal-oxide-semiconductor capacitors to detect interactions of Hf and Zr gate electrodes with SiO ₂ and ZrO ₂ ." Appl. Phys. Lett. <u>78</u> , 4166 (2001). V. Misra, M. Kulkarni, G. Heuss, H. Zhong, and H. Lazar, "Electrical and Material Properties of Metal Silicate Dielectrics and Metal Gate Electrodes for Advanced CMOS Devices," in Electrochemical Society Proceedings Vol. 2000-9, p. 291-98 (2000).							
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